

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07319 DT-33-19

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1329

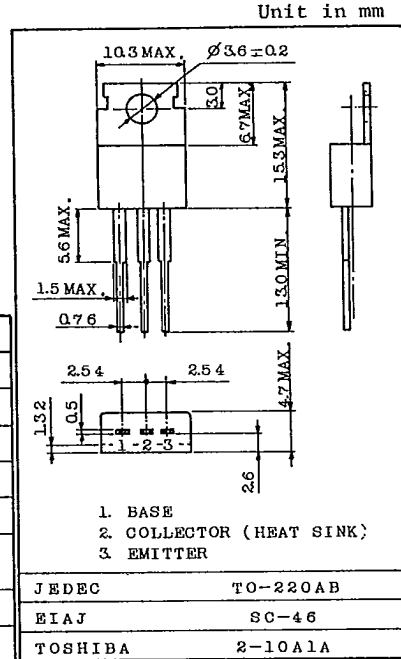
HIGH CURRENT SWITCHING APPLICATIONS.

FEATURES:

- . Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.4V(\text{Max.})$ at $I_C = -6A$
- . High Speed Switching Time : $t_{stg} = 1.0\mu s(\text{Typ.})$
- . Complementary to 2SC3346

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-80	V
Collector-Emitter Voltage	V _{CE0}	-80	V
Emitter-Base Voltage	V _{EB0}	-6	V
Collector Current	I _C	-12	A
Base Current	I _B	-2	A
Collector Power Dissipation (Tc=25°C)	P _C	40	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



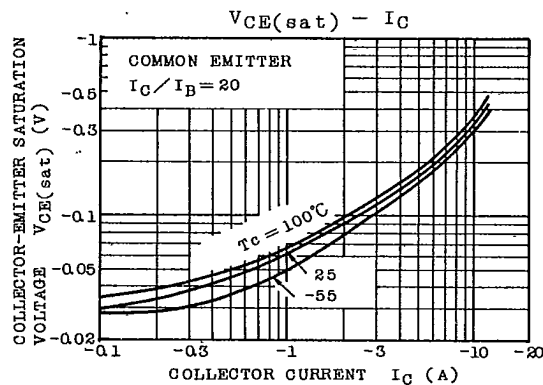
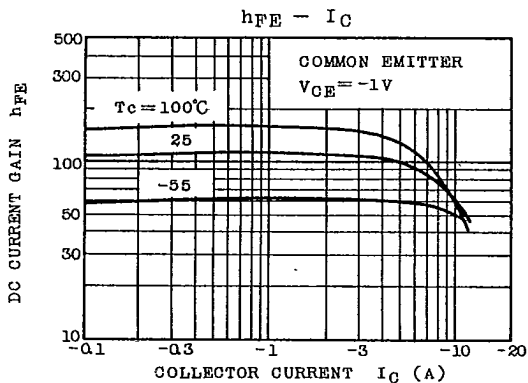
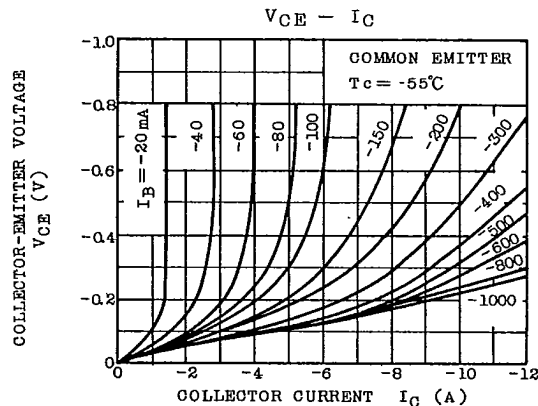
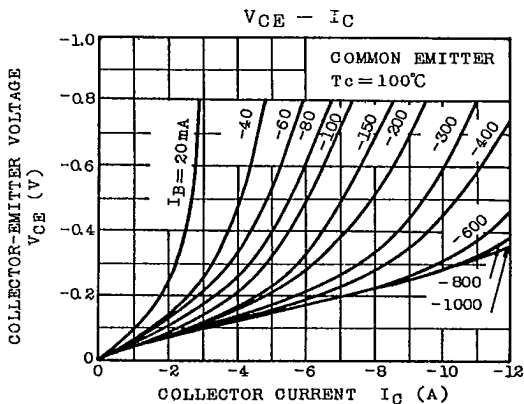
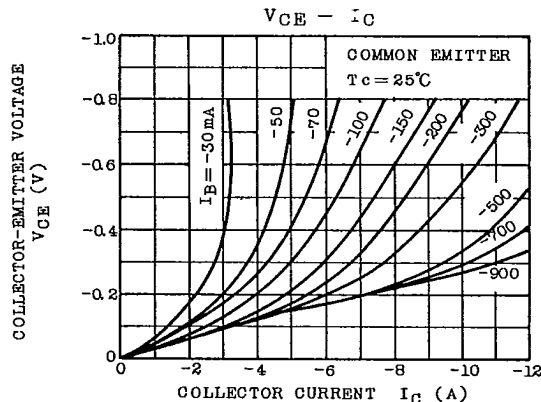
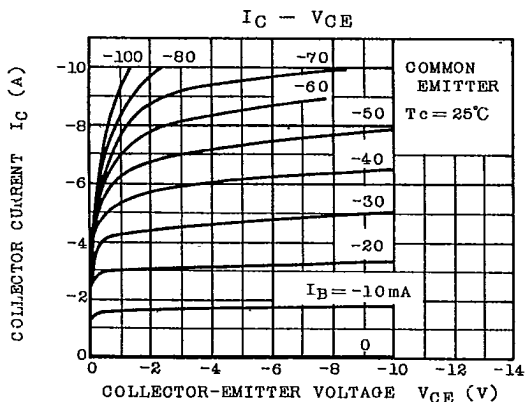
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CB0}	V _{CB} = -80V, I _E = 0	-	-	-10	μA
Emitter Cut-off Current		I _{EB0}	V _{EB} = -6V, I _C = 0	-	-	-10	μA
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	I _C = -50mA, I _B = 0	-80	-	-	V
DC Current Gain		h _{FE(1)} (Note)	V _{CE} = -1V, I _C = -1A	70	-	240	
		h _{FE(2)}	V _{CE} = -1V, I _C = -6A	40	-	-	
Saturation Voltage	Collector-Emitter	V _{CE(sat)}	I _C = -6A, I _B = -0.3A	-	-0.2	-0.4	V
	Base-Emitter	V _{BE(sat)}	I _C = -6A, I _B = -0.3A	-	-0.9	-1.2	
Transition Frequency		f _T	V _{CE} = -5V, I _C = -1A	-	50	-	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	-	400	-	pF
Switching Time	Turn-on Time	t _{on}		-	0.3	-	μs
	Storage Time	t _{stg}		-	1.0	-	
	Fall Time	t _f		-I _{B1} = I _{B2} = 0.3A DUTY CYCLE ≤ 1%	-	0.5	

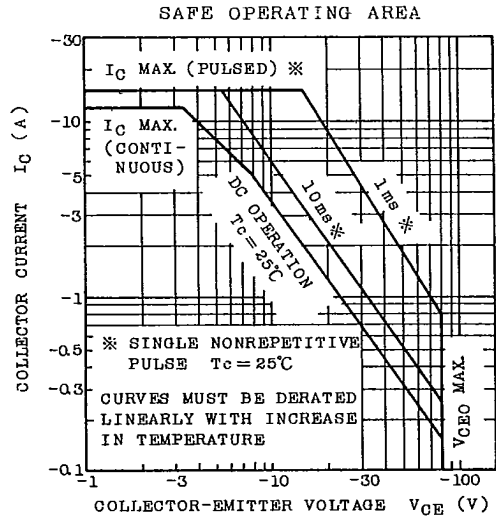
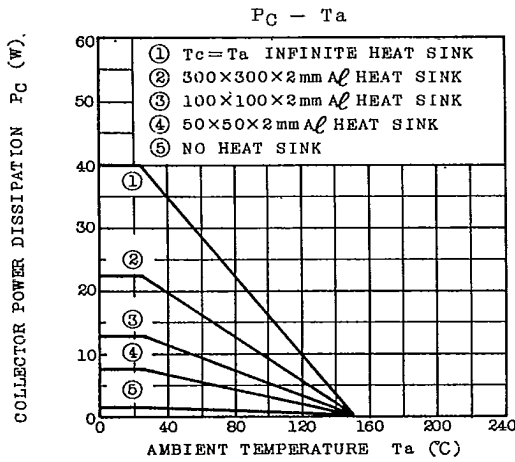
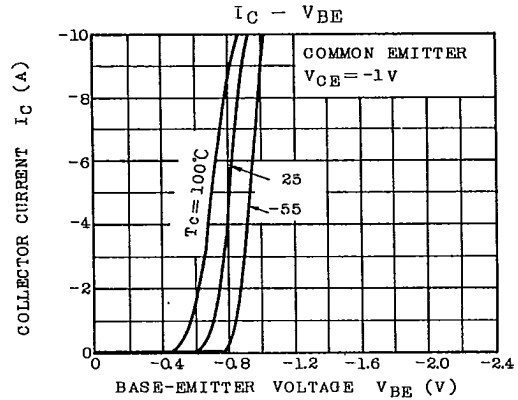
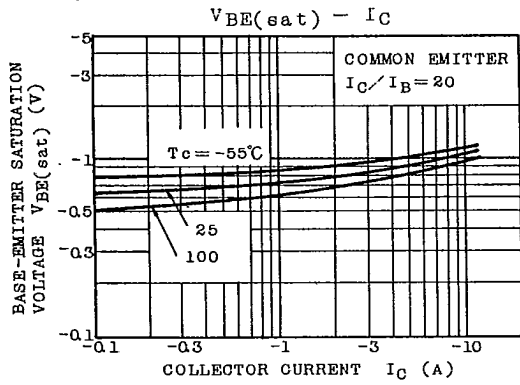
Note : h_{FE(1)} Classification O : 70 ~ 140, Y : 120 ~ 240

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